128Kx8 MONOLITHIC SRAM, SMD 5962-96691 (pending) *PRELIMINARY**

FEATURES

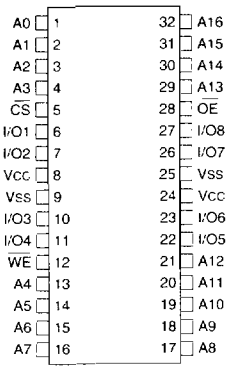
- Access Times 70, 85, 100, 120nS
- Revolutionary, Center Power/Ground Pinout JEDEC Approved
  - 32 lead Ceramic SOJ (Package 101)
- Evolutionary, Corner Power/Ground Pinout JEDEC Approved
  - 32 pin Ceramic DIP (Package 300)
  - 32 lead Ceramic SOJ (Package 101)
  - 32 lead Ceramic Flat Pack (Package 206)
- MIL-STD-883 Compliant Devices Available
- Commercial, Industrial and Military Temperature Range
- 5 Volt Power Supply
- Low Power CMOS
- 2V Data Retention Devices Available (Low Power Version)
- TTL Compatible Inputs and Outputs

* *This data sheet describes a product under development, not fully characterized, and is subject to change without notice*

REVOLUTIONARY PINOUT

32 CSOJ (DR)

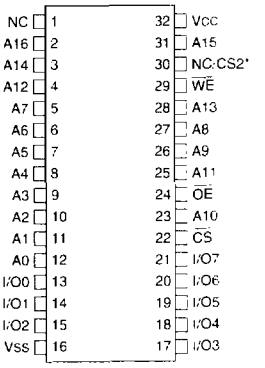
TOP VIEW



EVOLUTIONARY PINOUT

32 DIP
32 CSOJ (DE)
32 FLATPACK (FE)

TOP VIEW



* NC for single chip select devices
CS_2 for dual chip select devices

PIN DESCRIPTION

A_{0-16}	Address Inputs
I/O_{0-7}	Data Input/Output
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
V_{CC}	+5.0V Power
V_{SS}	Ground

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T_A	-55	+125	°C
Storage Temperature	T_{STG}	-65	+150	°C
Signal Voltage Relative to GND	V_G	-0.5	Vcc+0.5	V
Junction Temperature	T_J		150	°C
Supply Voltage	V_{CC}	-0.5	7.0	V

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	4.5	5.5	V
Input High Voltage	V_{IH}	2.2	V_{CC} + 0.3	V
Input Low Voltage	V_{IL}	-0.5	+0.8	V

TRUTH TABLE

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	H	H	Out Disable	High Z	Active
L	X	L	Write	Data In	Active

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Condition	Max	Unit
Input capacitance	C_{IN}	V_{IN} = 0V, f = 1.0MHz	20	pF
Output capicitance	C_{OUT}	V_{OUT} = 0V, f = 1.0MHz	20	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Sym	Conditions	-70		-85		-100		-120		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
Input Leakage Current	I_{LI}	V_{CC} = 5.5, V_{IN} = GND to V_{CC}		10		10		10		10	µA
Output Leakage Current	I_{LO}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, V_{OUT} = GND to V_{CC}		10		10		10		10	µA
Operating Supply Current	I_{CC}	$\overline{CS}$ = V_{IL}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		30		30		30		30	mA
Standby Current	I_{SB}	$\overline{CS}$ = V_{IH}, $\overline{OE}$ = V_{IH}, f = 5MHz, V_{CC} = 5.5		1.0		1.0		0.6		0.6	mA
Output Low Voltage	V_{OL}	I_{OL} = 2.1mA, V_{CC} = 4.5		0.4		0.4		0.4		0.4	V
Output High Voltage	V_{OH}	I_{OH} = -1.0mA, V_{CC} = 4.5	2.4		2.4		2.4		2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} -0.3V, V_{IL} = 0.3V

DATA RETENTION CHARACTERISTICS

(T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	-70			-85			-100			-120			Units
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Data Retention Supply Voltage	V_{DR}	$\overline{CS}$ V_{CC} -0.2V	2.0		5.5	2.0		5.5	2.0		5.5	2.0		5.5	V
Data Retention Current	I_{CCDR1}	V_{CC} = 3V		20	400		20	400		20	400		20	400	µA

AC CHARACTERISTICS

(V_{CC} = 5.0V, T_A = -55°C To +125°C)

Parameter Read Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t_{RC}	70		85		100		120		nS
Address Access Time	t_{AA}		70		85		100		120	nS
Output Hold from Address Change	t_{OH}	5		5		5		5		nS
Chip Select Access Time	t_{ACS}		70		85		100		120	nS
Output Enable to Output Valid	t_{OE}		35		45		50		60	nS
Chip Select to Output in Low Z	t_{CLZ}	5		5		5		5		nS
Output Enable to Output in Low Z	t_{OLZ}[1]	5		5		5		5		nS
Chip Disable to Output in High Z	t_{CHZ}[1]		25		25		35		35	nS
Output Disable to Output in High Z	t_{OHZ}[1]		25		25		35		35	nS

1. This parameter is guaranteed by design but not tested.

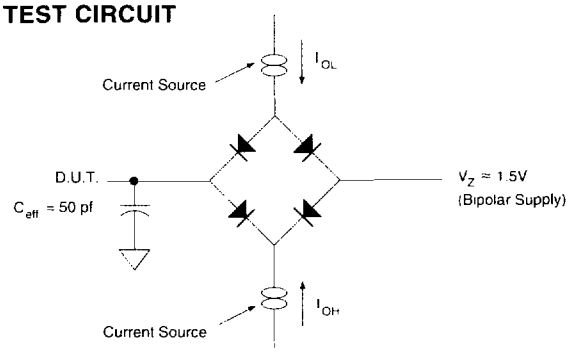
AC CHARACTERISTICS

(V_{CC} = 5.0V, T_A = -55°C To +125°C)

Parameter Write Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	70		85		100		120		nS
Chip Select to End of Write	t_{CW}	60		75		80		100		nS
Address Valid to End of Write	t_{AW}	60		75		80		100		nS
Data Valid to End of Write	t_{DW}	30		35		40		50		nS
Write Pulse Width	t_{WP}	50		55		70		80		nS
Address Setup Time	t_{AS}	0		0		0		0		nS
Address Hold Time	t_{AH}	5		5		5		5		nS
Output Active from End of Write	t_{OW}[1]	5		5		5		5		nS
Write Enable to Output in High Z	t_{WHZ}		25		30		35		35	nS
Data Hold Time	t_{DH}	0		0		0		0		nS

1. This parameter is guaranteed by design but not tested.

AC TEST CIRCUIT



AC TEST CONDITIONS

Parameter	Typ	Unit
Input Pulse Levels	V_{IL} = 0, V_{IH} = 3.0	V
Input Rise and Fall	5	nS
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:

V_Z is programmable from -2V to +7V

I_{OL} & I_{OH} programmable from 0 to 16mA

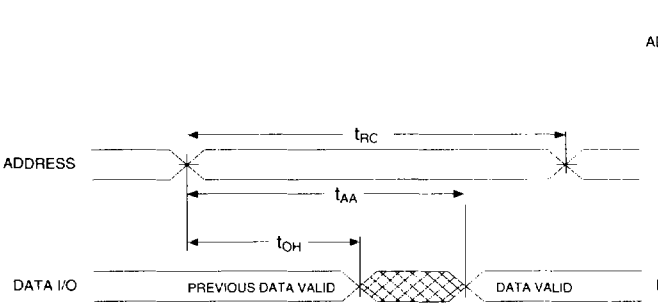
Tester Impedance Z_0 = 75

V_Z is typically the midpoint of V_{OH} and V_{OL}.

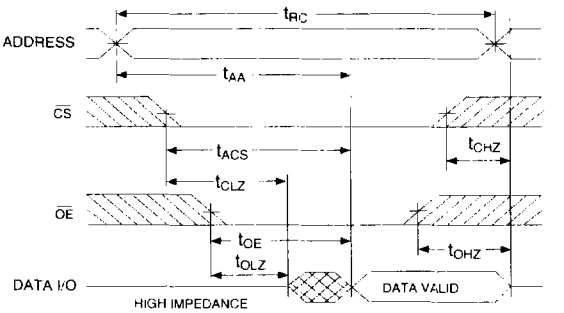
I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit

ATE tester includes jig capacitance.

TIMING WAVEFORM - READ CYCLE

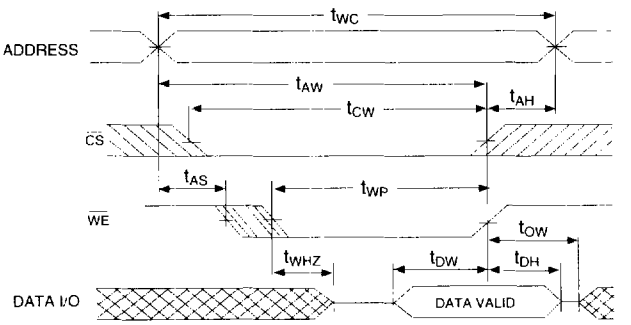


READ CYCLE 1 ($\overline{CS}$ = $\overline{OE}$ = V_{IL}, $\overline{WE}$ = V_{IH})



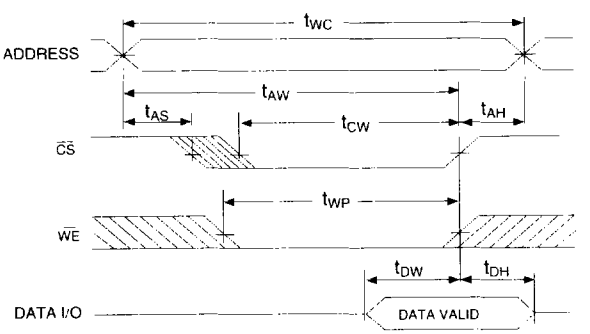
READ CYCLE 2 ($\overline{WE}$ = V_{IH})

WRITE CYCLE - $\overline{WE}$ CONTROLLED



WRITE CYCLE 1, $\overline{WE}$ CONTROLLED

WRITE CYCLE - $\overline{CS}$ CONTROLLED



WRITE CYCLE 2, $\overline{CS}$ CONTROLLED

DATA RETENTION CHARACTERISTICS

(T_A = -55°C to +125°C)

LOW POWER VERSION ONLY

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Data Retention Supply Voltage	V_{DR}	$\overline{CS}$ V_{CC} -0.2V	2.0		5.5	V
Data Retention Current	I_{CCDR3}	V_{CC} = 3V		10	100	µA

ORDERING INFORMATION

W M S 128K8 X - XXX X X X

SPECIAL PROCESSING:
E = Epitaxial Layer

DEVICE GRADE:
M = Military Screened -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

PACKAGE:
C = 32 Pin Ceramic .600" DIP (Package 300)
DE = 32 Lead Ceramic SOJ (Package 101) Evolutionary
DJ = 36 Lead Ceramic SOJ (Package 100)
DR = 32 Lead Ceramic SOJ (Package 101) Revolutionary
F = 36 Lead Ceramic Flat Pack (Package 200)
FE = 32 Lead Ceramic Flat Pack (Package 206)

ACCESS TIME in nS

IMPROVEMENT MARK
C = Dual Chip Select Device
L = Low Power for 2V Data Retention

ORGANIZATION, 128K x 8

SRAM

MONOLITHIC

WHITE MICROELECTRONICS

DEVICE TYPE	SPEED	PACKAGE	SMD NO.
128K x 8 SRAM Monolithic	120nS	32 lead SOJ Revol (DR)	5962-96691 01HUX*
128K x 8 SRAM Monolithic	**100nS**	**32 lead SOJ Revol (DR)**	**5962-96691 02HUX***
128K x 8 SRAM Monolithic	85nS	32 lead SOJ Revol (DR)	5962-96691 03HUX*
128K x 8 SRAM Monolithic	70nS	32 lead SOJ Revol (DR)	5962-96691 04HUX*
128K x 8 SRAM Monolithic	120nS	32 lead SOJ Evol (DE)	5962-96691 01HTX*
128K x 8 SRAM Monolithic	**100nS**	**32 lead SOJ Evol (DE)**	**5962-96691 02HTX***
128K x 8 SRAM Monolithic	85nS	32 lead SOJ Evol (DE)	5962-96691 03HTX*
128K x 8 SRAM Monolithic	70nS	32 lead SOJ Evol (DE)	5962-96691 04HTX*
128K x 8 SRAM Monolithic	120nS	32 pin DIP (C)	5962-96691 01HYX*
128K x 8 SRAM Monolithic	**100nS**	**32 pin DIP (C)**	**5962-96691 02HYX***
128K x 8 SRAM Monolithic	85nS	32 pin DIP (C)	5962-96691 03HYX*
128K x 8 SRAM Monolithic	70nS	32 pin DIP (C)	5962-96691 04HYX*
128K x 8 SRAM Monolithic	120nS	36 lead SOJ (DJ)	5962-96691 01HZX*
128K x 8 SRAM Monolithic	**100nS**	**36 lead SOJ (DJ)**	**5962-96691 02HZX***
128K x 8 SRAM Monolithic	85nS	36 lead SOJ (DJ)	5962-96691 03HZX*
128K x 8 SRAM Monolithic	70nS	36 lead SOJ (DJ)	5962-96691 04HZX*
128K x 8 SRAM Monolithic	120nS	36 lead Flatpack (F)	5962-96691 01HXX*
128K x 8 SRAM Monolithic	**100nS**	**36 lead Flatpack (F)**	**5962-96691 02HXX***
128K x 8 SRAM Monolithic	85nS	36 lead Flatpack (F)	5962-96691 03HXX*
128K x 8 SRAM Monolithic	70nS	36 lead Flatpack (F)	5962-96691 04HXX*

* Pending